

ERASING METHOD IN NON-VOLATILE MEMORY DEVICE

ABSTRACT OF THE DISCLOSURE

A method for performing an erase operation in a memory cell. A first voltage
5 and a second voltage are applied to the source and drain regions, respectively, for a
predetermined erase time; and the first and second voltages are switched with each other
between the source and drain regions at least one time for the erase time. Thereby, hole
is easily injected to the source and drain regions and a channel lateral surface, and a
uniform and high-speed erase operation is archived.